प्रश्नपुस्तिका क्रमांक Question Booklet No.

प्रश्नपुस्तिका सीरीज Question Booklet Series C

M.Sc (Electronics) First Semester, Examination, February/March-2022 ELC-101(N) Physics of Electronics Materials

Time: 1:30 Hours Maximum Marks-100

जब तक कहा न जाय, इस प्रश्नपुस्तिका को न खोलें

- निर्देश: 1. परीक्षार्थी अपने अनुक्रमांक, विषय एवं प्रश्नपुस्तिका की सीरीज का विवरण यथास्थान सही— सही भरें, अन्यथा मृल्यांकन में किसी भी प्रकार की विसंगति की दशा में उसकी जिम्मेदारी स्वयं परीक्षार्थी की होगी।
 - 2. इस प्रश्नपुस्तिका में 100 प्रश्न हैं, जिनमे से केवल 75 प्रश्नों के उत्तर परीक्षार्थियों द्वारा दिये जाने है। प्रत्येक प्रश्न के चार वैकल्पिक उत्तर प्रश्न के नीचे दिये गये हैं। इन चारों में से केवल एक ही उत्तर सही है। जिस उत्तर को आप सही या सबसे उचित समझते हैं, अपने उत्तर पत्रक (O.M.R. ANSWER SHEET)में उसके अक्षर वाले वृत्त को काले या नीले बाल प्वांइट पेन से पूरा भर दें। यदि किसी परीक्षार्थी द्वारा निर्धारित प्रश्नों से अधिक प्रश्नों के उत्तर दिये जाते हैं तो उसके द्वारा हल किये गये प्रथमतः यथा निर्दिष्ट प्रश्नोत्तरों का ही मूल्यांकन किया जायेगा।
 - प्रत्येक प्रश्न के अंक समान हैं। आप के जितने उत्तर सही होंगे, उन्हीं के अनुसार अंक प्रदान किये जायेंगे।
 - 4. सभी उत्तर केवल ओ०एम०आर० उत्तर पत्रक (O.M.R. ANSWER SHEET) पर ही दिये जाने हैं। उत्तर पत्रक में निर्धारित स्थान के अलावा अन्यत्र कहीं पर दिया गया उत्तर मान्य नहीं होगा।
 - 5. ओ॰एम॰आर॰ उत्तर पत्रक (O.M.R. ANSWER SHEET) पर कुछ भी लिखने से पूर्व उसमें दिये गये सभी अनुदेशों को सावधानीपूर्वक पढ़ लिया जाय।
 - 6. परीक्षा समाप्ति के उपरान्त परीक्षार्थी कक्ष निरीक्षक को अपनी प्रश्नपुस्तिका बुकलेट एवं ओ०एम०आर० शीट पृथक-पृथक उपलब्ध कराने के बाद ही परीक्षा कक्ष से प्रस्थान करें।
 - 7. निगेटिव मार्किंग नहीं है।
- महत्वपूर्ण : प्रश्नपुस्तिका खोलने पर प्रथमतः जाँच कर देख लें कि प्रश्नपुस्तिका के सभी पृष्ठ भलीभाँति छपे हुए हैं। यदि प्रश्नपुस्तिका में कोई कमी हो, तो कक्ष निरीक्षक को दिखाकर उसी सीरीज की दूसरी प्रश्नपुस्तिका प्राप्त कर लें।

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Rough Work / रफ कार्य

1.	For a semiconductor-based light source, it should be a.
	(A) Direct bandgap semiconductor
	(B) Indirect direct bandgap semiconductor
	(C) Either direct bandgap or indirect bandgap
	(D) The semiconductor can not be used as a light source
2.	The B/H curve can be used to determine?
	(A) Iron loss
	(B) Eddy current loss
	(C) Hysteresis loss
	(D) Voltage loss
3.	The electrical conductivity of metals is typically of the order of (in ohm ⁻¹ m ⁻¹)
	(A) 10^7
	(B) 10^5
	(C) 10^{-4}
	(D) 10^{-6}
4.	If the permeability is high, the hysteresis loss is
	(A) Infinity
	(B) Zero
	(C) Infinity
	(D) Low
5.	In a magnetic material hysteresis loss takes place primarily due to?
	(A) Rapid reversals of its magnetisation
	(B) Flux density lagging behind magnetising force
	(C) Molecular friction
	(D) Its high retentivity

6.	The area of his hysteresis loss is a measure of
	(A) Permittivity
	(B) Permeance
	(C) Energy loss per cycle
	(D) Magnetic flux
7.	Fermi-Dirac (FD) statistics governs.
	(A) Fermions
	(B) Free electrons
	(C) Fermions & free electrons
	(D) None
8.	Which of the following is a radiative semiconductor.
	(A) Silica
	(B) Gallium Arsenide
	(C) Germanium
	(D) None of the above
9.	Hall voltage is developed due to the
	(A) Change in the magnetic field
	(B) Change in the electric field
	(C) Polarization of charges
	(D) None of the above

- 10. In the process of Czochralski method which of the following relation is appropriate between the melt and the growing crystals?
 - (A) Melt and the growing crystals are usually not related to each other
 - (B) Melt and the growing crystals are usually rotated counterclockwise
 - (C) Melt and the growing crystals are usually rotated clockwise
 - (D) Melt and the growing crystals are usually kept at a constant position
- 11. A soft magnetic material is having
 - (A) Low hysteresis loss
 - (B) Copper loss
 - (C) High hysteresis loss
 - (D) None of these
- 12. Which of the following method has been used to prepare the single crystals of CaO using plasma torch?
 - (A) Stock Barger method
 - (B) Zone melting method
 - (C) Verneuil flame fusion method
 - (D) Bridgman method
- 13. For a core having a relative permeability $\mu_{r'}$ magnetic dipole moment per unit volume M and field strength H, the flux density B is.
 - (A) $B = \mu_r(H+M)$
 - (B) $B = \mu_0(H+M)$
 - (C) $B = \mu_0 \mu_r (H+M)$
 - (D) $B = \mu_0 \mu_r (H-M)$

14. In an homogeneous dielectric subjected to an electric field E, the dipole moment per unit volume is $\in_0(\in_r-1)$ E. (A) True (B) False (C) Ambiguous statement (D) None of these 15. The amount of time between the creation and recombination of a free electron and hole is called. (A) Relaxation time (B) Life time (C) Lorentz time (D) Collision time 16. Hall effect is observed in a specimen (metal or semi conductor) when it is carrying current and is placed in a magnetic field. The resultant electric field inside the specimen is (A) Normal to both current and magnetic field (B) In the same direction as current (C) In a direction anti parallel to magnetic field (D) None of the above Permeability is analogous to 17. (A) Resistivity (B) Retentivity

(C) Conductivity

(D) Coercivity

18.	For dielectrics in alternating field, polarizability e is a complex quantity. The
	imaginary part of e is zero for.
	(A) $\omega = 0$
	(B) ω→∞
	(C) $\omega = 0$ and $\omega \rightarrow \infty$
	(D) $\omega = \text{natural frequency } \omega_0$
19.	In the magnetostriction method, a ferromagnet substance changes its shape and size
	when placed in a
	(A) Magnetic field
	(B) Alternating current
	(C) Electric field
	(D) (A) and (B)
20.	For constructive interference.
	(A) The phase difference should be constant
	(B) The phase difference should be zero
	(C) The two waves should be out of phase
	(D) None of the above
21.	Give the thickness range of the film used in thin film technology.
	(A) 0.5-2.5 mils
	(B) 0.02-8 mils
	(C) 10-20 mils
	(D) 0.05-0.07 mils
22.	Diamagnetic substance are those having a permeability
	(A) less than free space
	(B) More than free space
	(C) Equal to free space
	(D) Much greater than free space

23. Which of the following process is involve in thick film technology (A) Silk screening (B) Ceramic firing (C) Screen printing (D) All of the mentioned 24. Soft magnetic materials have low (A) Resistivity (B) Permeability (C) Conductivity (D) Coercive force 25. Which technology is used to get cheap resistors and capacitors? (A) Thin and thick film technology (B) Thick film technology (C) Thin film technology (D) None of the mentioned 26. Which of the following monomers form biodegradable polymers? (A) 3-hydroxybutanoic acid+3-hydroxypentanoic acid (B) Glycine + amino caproic acid (C) Ethylene glycol + phthalic acid (D) (A) and (B) 27. In paramagnetic materials (A) Permanent magnetic dipoles exist but the interaction between neighbouring dipoles is negligible (B) Permanent magnetic dipole do not exist (C) Permanent magnetic dipole moment may or may not exist

dipoles is very strong

(D) Permanent magnetic dipoles exist and the interaction between neighbouring

28.	Magnetism of a material can be destroyed by
	(A) Heating
	(B) Hammering
	(C) By inductive action of another magnet
	(D) By all above methods
29.	Ferrites are a sub-group of
	(A) Non-magnetic materials
	(B) Ferro-magnetic materials
	(C) Paramagnetic materials
	(D) Ferri-magnetic materials
30.	Oscillations are damped due to the presence of
	(A) Linear motion
	(B) Restoring force
	(C) Frictional force
	(D) Mechanical force
31.	When an electric field E is applied to solid and liquid insulating materials, the
	internal field E _i acting at the location of atom is such that.
	(A) $E_i = E$
	(B) $E_i > E$
	(C) $E_i < E$
	(D) E _i may be equal to or less than E
32.	The relative permeability of materials is not constant.
	(A) Diamagnetic
	(B) Paramagnetic
	(C) Ferromagnetic
	(D) Insulating

33.	Non-reactive sputtering is usually conducted at a pressure of:
	(A) 0.001-0.1Pa
	(B) 0.01-1.0 Pa
	(C) 0.1-10.0 Pa
	(D) 1.0-100 Pa
34.	The minority carrier life time and diffusion constant in a semiconduction material
	are $100 \mu s$ and $100 cm^2/s$ respectively. The diffusion length of carries is.
	(A) 0.1cm
	(B) 0.01cm
	(C) 0.141cm
	(D) 1cm
35.	Two materials having temperature coefficients of 0.004 and 0.0004 respectively are
	joined in series. The overall temperature coefficient is likely to be.
	(A) 0.08
	(B) 0.04
	(C) 0.001
	(D) 0.0001
36.	The hysteresis loss is.
	(A) Proportional to frequency
	(B) Independent of frequency
	(C) Proportional to (frequency) ²
	(D) Proportional to $\frac{1}{frequency}$

37.	Which of the following is true for the resultant polymer product formed, when
	molecules of pthalic acid react with molecules of glycerol?
	(A) Branch polymer
	(B) Linear polymer
	(C) Cross-link polymer
	(D) None of the mentioned
38.	Which type of material expands and contract in response to an applied electric
	field?
	(A) Advanced material
	(B) Smart material
	(C) Biomaterial
	(D) Nanomaterial
39.	With an increase in temperature, magnetic susceptibility of a ferromagnetic
	material
	(A) Increases
	(B) First increases and then decreases
	(C) Remains constant
	(D) Decreases
40.	In sputtering, the target serves as the:
	(A) Cathode
	(B) Anode
	(C) Neutral electrode
	(D) None of the above

41.	In ferroelectric material, the spontaneous polarization vanishes above
	(A) A. Transition temperature
	(B) Debye temperature
	(C) Fermi temperature
	(D) Curie temperature
42.	Chemical vapour deposition is a method which is used to obtain which of the
	following substance?
	(A) Semiconductors
	(B) Crystalline semiconductor
	(C) Conducting compounds
	(D) Non conducting polymers
43.	What will be the phase composition of a phase system
	(A) The composition of each phase is different throughout the phase diagram
	(B) The composition of each phase is same throughout the phase diagram
	(C) Varies from molecule to molecule
	(D) Contains more than one composition in the entire phase diagram
44.	The conduction band of a semiconductor material may be
	(A) Completely filled
	(B) Partially filled
	(C) Empty
	(D) None
45.	What are the external parameters that affect the phase structure?
	(A) Pressure, Composition
	(B) Temperature, Pressure
	(C) Temperature, Pressure, Composition
	(D) Temperature, Composition
	-

46.	Superconducting materials are being used in the Superconducting Super Collider to
	(A) Cool the particles
	(B) Minimize electrical power consumption
	(C) Maximize the acceleration potentials
	(D) Provide radiation shielding
47.	What is the factor that differentiates between Electroless deposition and cathodi
	deposition?
	(A) Anode
	(B) Nature of electrolyte
	(C) External field
	(D) Cathode
48.	In electrostriction, when an electric field is applied, polarization may change th
	of the material.
	(A) Resistance
	(B) Temperature coefficient
	(C) Dimensions
	(D) Resistivity
49.	Packing efficiency of a crystal structure is the ratio of:
	(A) Volume occupied by particles to the total volume of the unit cell
	(B) Volume occupied by voids to that by particles
	(C) Total volume of the unit cell to the volume occupied by particles
	(D) Volume occupied by particles to that by voids
50.	Which of the following unit cells do not exist for tetragonal lattices?
	(A) Primitive centered unit cell
	(B) Face centered unit cell
	(C) Body centered unit cell
	(D) All of the mentioned exist

51.	The density of silver is 10.5 g/cm ³ and its atomic weight is 108. If each atom
	contributes one electron for conduction, what is the fermi energy?
	(A) 2.12 eV
	(B) 3.31 eV
	(C) 5.51 eV
	(D) 4.69 eV
52.	An electrical current in a superconducting ring will theoretically flow unchanged
	for:
	(A) Several milliseconds
	(B) Forever
	(C) Several weeks
	(D) A second
53.	The hard super conductors are those in which the ideal behaviour is seen up to a
	critical magnetic field
	(A) Higher
	(B) Moderate
	(C) Lower
	(D) Zero
54.	In piezoelectric material, energy is converted into electrical energy
	(A) Solar
	(B) Mechanical
	(C) Heat
	(D) Chemical
55.	In Hall effect, the output voltage produced across the crystal is due to
	(A) Drop across the crystal is due to the current passed through it
	(B) Induced voltage by the applied magnetic field
	(C) Movement of charge carriers towards one end
	(D) All of the above
	(D) All of the above

56.	The magnitude and direction of lattice distortion are expressed in terms of which
	vector?
	(A) Burger vector
	(B) Edge vector
	(C) Dislocation vector
	(D) Screw vector
57.	London dispersion forces exist inmolecules.
	(A) Ionic
	(B) Covalent
	(C) Monoatomic
	(D) Non-Polar
58.	Fermi-Dirac statistics is for the
	(A) Particles with integral spin
	(B) Particles with half integral spin
	(C) Symmetrical Particles
	(D) Distinguishable particles
59.	The momentary attraction between the molecules of a liquid caused by
	instantaneous dipole and induced-dipole attractions are calledforces.
	(A) French
	(B) Polar
	(C) Van der Waals
	(D) London
60.	In ferroelectric material, hysteresis loop is a function of applied electric field.
	(A) Non-linear
	(B) Linear
	(C) Parabolic
	(D) Exponential

61.	What is mobility?
	(A) Ease of carrier drift
	(B) Ease of movement
	(C) Ease of current flow
	(D) Ease of access to the junction
62.	In the Hall Effect, the directions of electric field and magnetic field are parallel to
	each other The statement is
	(A) True
	(B) False
	(C) Ambiguous Statement
	(D) None of these
63.	The shifting of electrons in super conductors is prevented by
	(A) Quantum effect
	(B) Energy barrier
	(C) Orbitals
	(D) Threshold energy level
64.	Which of the following formulae doesn't account for correct expression for J?
	(A) μH
	(B) I/wd
	(C) σE
	(D) ρv
65.	Which of the following statement is correct about smectic liquid crystals?
	(A) The flow readily thansmectic liquid crystals
	(B) They have liquid like character
	(C) Their viscosity is lower than that of liquids
	(D) All of these

66.	Calculate the hall voltage when the Electric Field is 5V/m and height of the
	semiconductor is 2cm
	(A) 0.1V
	(B) 10V
	(C) 1V
	(D) 0.01V
67.	Drift current is due to
	(A) Applied electric field over a given distance
	(B) Random motion of holes
	(C) Recombination of holes and electrons
	(D) Random motion of electrons
68.	Nematic is a type of liquid crystal which is based upon
	(A) Surface area
	(B) Molecules
	(C) Ordering
	(D) Surface tension
69.	Which of the following term is not valid for dielectric materials
	(A) Dielectric constant
	(B) Permittivity
	(C) Polarization
	(D) Permeability
70.	Cholesteryl benzoate is an example ofcrystal
	(A) Smectic
	(B) Nematic
	(C) Solid
	(D) Cholesteric

71.	In superconductors, the Fermi energy level is
	(A) Midway between the ground state and first excited state
	(B) Above first excited state
	(C) At first excited state
	(D) Below the ground state
72.	Which of the following parameters can't be found with Hall Effect?
	(A) Conductivity
	(B) Polarity
	(C) Area of the device
	(D) Carrier concentration
73.	Which of the following is a crystalline solid?
	(A) Copper wire
	(B) Rubber ball
	(C) Glass bottle
	(D) Polythene beg
74.	In liquid crystals, temperature affect the
	(A) Magnetic field
	(B) Electric field
	(C) Neutron field
	(D) Electromagnetic field
75.	Fermi-Dirac statistics cannot be applied to
	(A) Fermions
	(B) Electrons
	(C) Protons
	(D) Photons

76. Which of the following statements is not valid for relative permittivity (A) It is dimensionless (B) Its value for all substances is more than one (C) It is not equal to unity for vacuum (D) None of these The equation $J_n = qn\mu_n E (A/cm^2)$ represents 77. (A) Diffusion current density (B) Drift current (C) Diffusion current (D) Drift current density The Hall coefficient of a specimen is 3.66×10⁻⁴ m³C-¹. If it's resistivity is 8.93×10⁻¹ 78. ³ Ω m, what will be its mobility? (A) $0.01 \text{ m}^2\text{V}$ (B) $0.02 \text{ m}^2\text{V}$ (C) $0.03 \text{ m}^2\text{V}$ (D) $0.04 \text{ m}^2\text{V}$ The minimum amount of current passed through the body of superconductor in 79. order to destroy the superconductivity is called (A) Induced current (B) Critical current (C) Eddy current (D) Hall current 80. Which of the following is used to make Light Emitting Diodes (LED)? (A) Direct Bandgap Semiconductors (B) Small Bandgap

(C) Large Bandgap

(D) Indirect Bandgap Semiconductors

81.	Which of the following properties is generally exhibited by amorphous solids?
	(A) Glass-transition
	(B) Equal strength of all bonds
	(C) Anisotropy
	(D) All of the mentioned
82.	The random motion of holes and free electrons due to thermal agitation is called
	(A) Ionization
	(B) Pressure
	(C) Diffusion
	(D) None of the above
83.	Interaction between neighboring dipoles, is equal and opposite in—material.
	(A) Ferromagnetic
	(B) Ferriomagnetic
	(C) Antiferromagnetic
	(D) Paramagnetic
84.	Thermal conductivity is defined as the heat flow per unit time
	(A) When the temperature gradient is unity
	(B) Across the wall with no temperature
	(C) Through a unit thickness of the wall
	(D) Across unit area where the temperature gradient is unity
85.	With an increase in bond length, bond energy:
	(A) increases
	(B) Decreases
	(C) May either increase or decrease
	(D) Does not change

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An n-type semiconductor is
(A) Positively charged
(B) Electrically neutral
(C) Negatively charged
(D) None of the above
Which of the following Bravais lattices exist as face centered unit cell?
(A) Orthorhombic
(B) Tetragonal
(C) Monoclinic
(D) None of the mentioned
Ferrites show
(A) Diamagnetism
(B) Ferromagnetism
(C) Both (A) &(B)
(D) None of (A) & (B)
A semiconductor has temperature coefficient of resistance.
(A) Negative
(B) Positive
(C) Zero
(D) None of above
When the atomic magnetic moments are randomly oriented in a solid its magnetic
behavior is termed as
(A) Anti-ferromagnetic
(B) Paramagnetic
(C) Ferromagnetic
(D) D. Diamagnetic

91.	What is phase?
	(A) The substance which is both physically distinct and chemically homogenous
	(B) The substance which is homogenous chemically
	(C) Substance which is both physically distinct and chemically heterogeneous
	(D) The substance which is physically distinct
92.	In orientational polarization, rotation of the permanent dipole moments is
	direction of the applied field.
	(A) In opposite
	(B) In the
	(C) In parallel with the
	(D) None
93.	The strength of a semiconductor crystal comes from
	(A) Forces between nuclei
	(B) Forces between protons
	(C) Electron-pair bonds
	(D) None of the above
94.	The dielectric loss is affected by
	(A) Presence of humidity
	(B) Voltage and temperature increase
	(C) Frequency of applied voltage
	(D) All of the above
95.	Which type of defect are point defects?
	(A) One dimensional defect
	(B) Two dimensional defect

(C) Three dimensional defect

(D) Zero dimensional defect

96.	Whi	ch of the following behaves as an insulator.
	(A)	Silver
	(B)	Diamond
	(C)	Silicon
	(D)	Germanium
97.	Whi	ch of the following is a secondary bond?
	(A)	Metallic bond
	(B)	Covalent bond
	(C)	Hydrogen bond
	(D)	Ionic bond
98.	The	magnetic lines of force cannot penetrate the body of a superconductor, a
	pher	nomenon is known as
	(A)	Meissner effect
	(B)	BCS theory
	(C)	Isotopic effect
	(D)	London theory
99.	Whi	ch of the following are the properties of superconductors?
	(A)	They are diamagnetic in nature
	(B)	They have zero resistivity
	(C)	They have infinite conductivity
	(D)	All of the above
100.	All 1	piezo-electric materials are
	(A)	Dielectric materials
	(B)	Ferroelectric materials
	(C)	Ferrielectric materials
	(D)	None

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- 1. Examinee should enter his / her roll number, subject and Question Booklet Series correctly in the O.M.R. sheet, the examinee will be responsible for the error he / she has made.
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- 3. Every question has same marks. Every question you attempt correctly, marks will be given according to that.
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